

ABSTRACT

The present invention is a method capable of fabricating photomasks with improved control of gate line width wafers. More specifically a method is provided to determine a mask correction unit 3 based on pattern space dependency 7 in the pattern obtained in the photolithographic process and etching process, and correct the mask fabrication design data 1 utilizing the mask correction unit 3, and fabricate photomasks using photolithographic equipment.

0982305-101701